



Simulation study in Design of Miniaturized Mid-Infrared Sensors

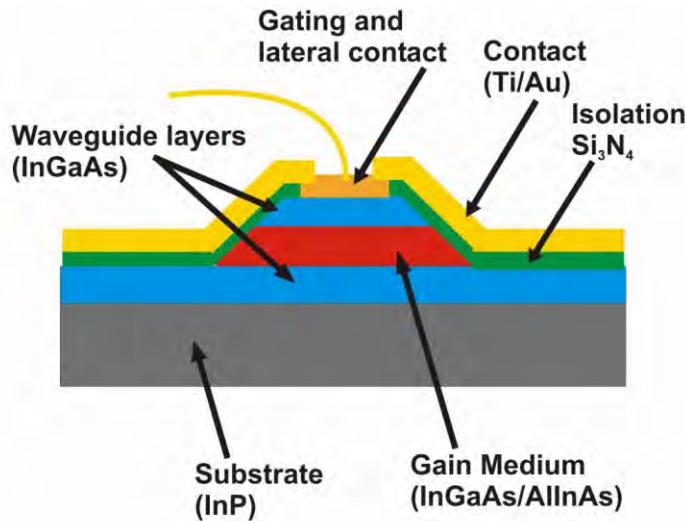
X. Wang, S-S. Kim, B. Mizaikoff*



- MIR sensors combined with quantum cascade lasers (QCL)
- MIR $\text{GaAs}/\text{Al}_{0.2}\text{Ga}_{0.8}\text{As}$ waveguides
 - Strip waveguides
 - Slot waveguides
- Simulation studies on MIR waveguide design

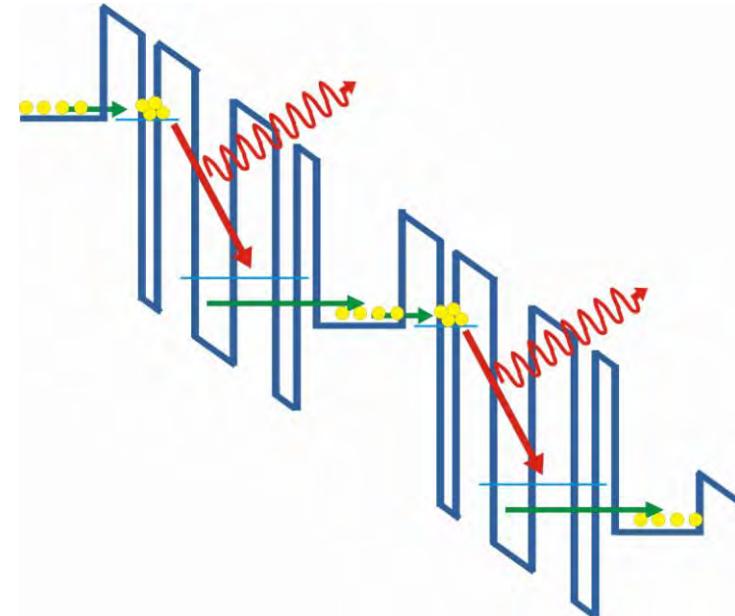
Quantum Cascade Lasers (QCL)

1994 - Breakthrough in IR light source technology



- Layers of semiconductor materials create a quantum heterostructure
- Common materials are:
InGaAs/AlInAs/InP and GaAs/AlGaAs

- Photons produced by intersubband transitions rather than recombination processes
- Layer dimensions dictate energy levels in heterostructure (quantum wells)
- Cascaded structures may produce multiple photons per electron

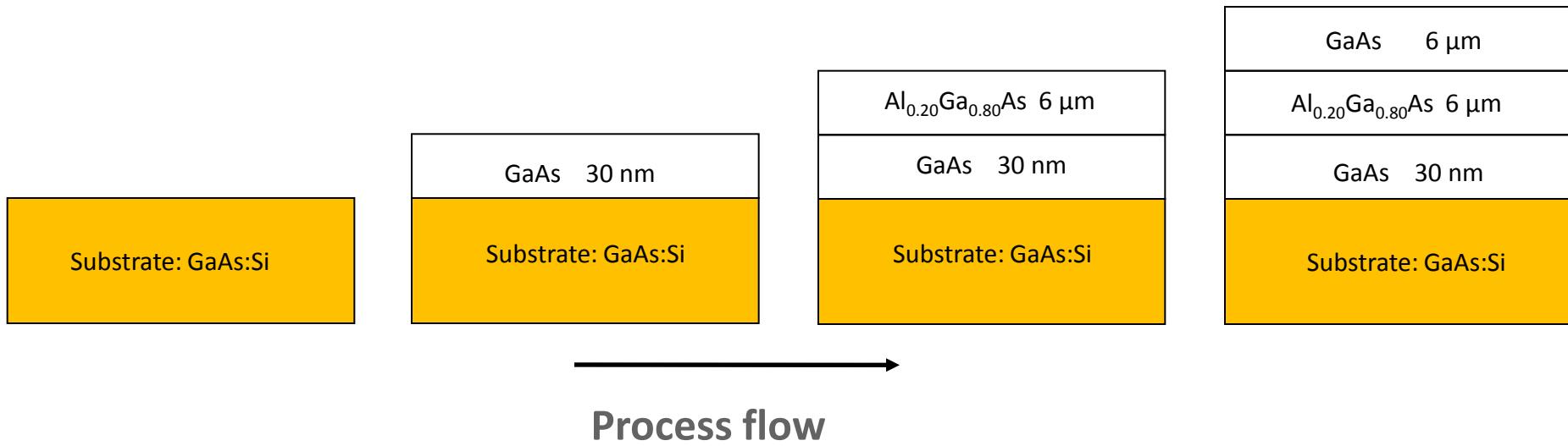


J.Faist, et al., Science, 264, 553 (1994)

3

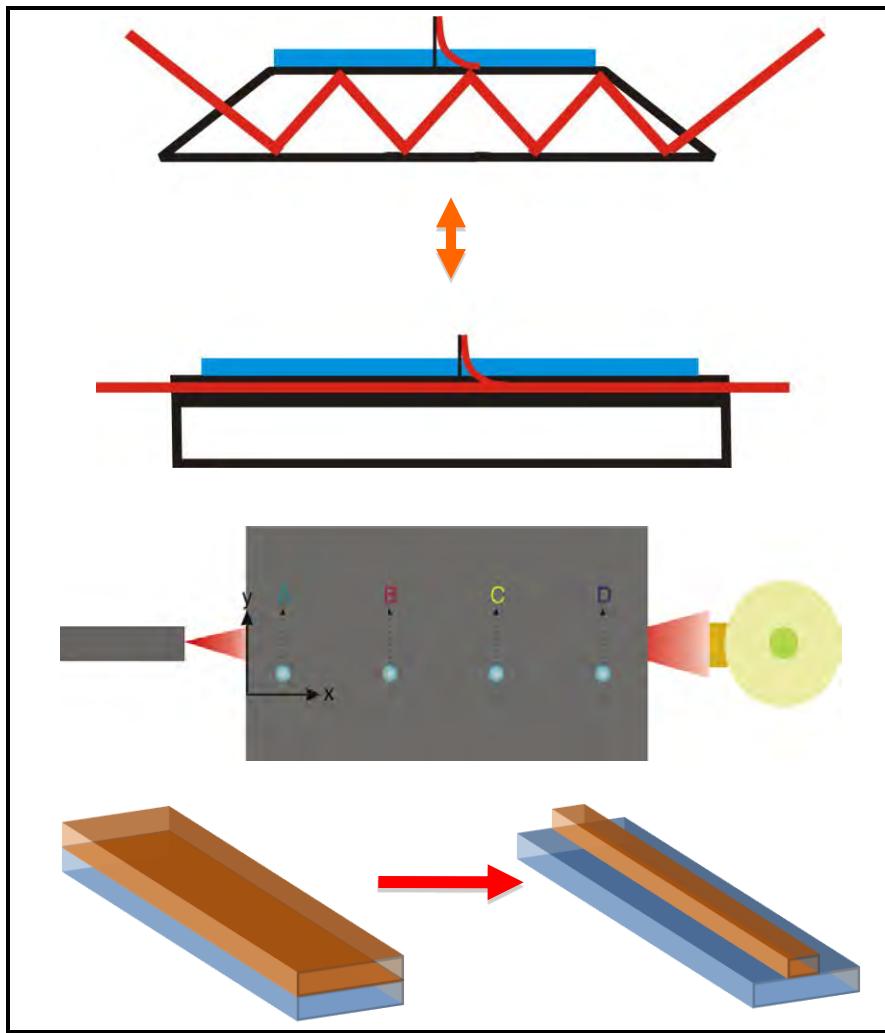
Growth parameters

- MOVPE AIX – 200
- Materials used:
TMGa, TEGa, TMAl, AsH₃,
- Horizontal reactor at 100 mbar
- T_G = 750° C

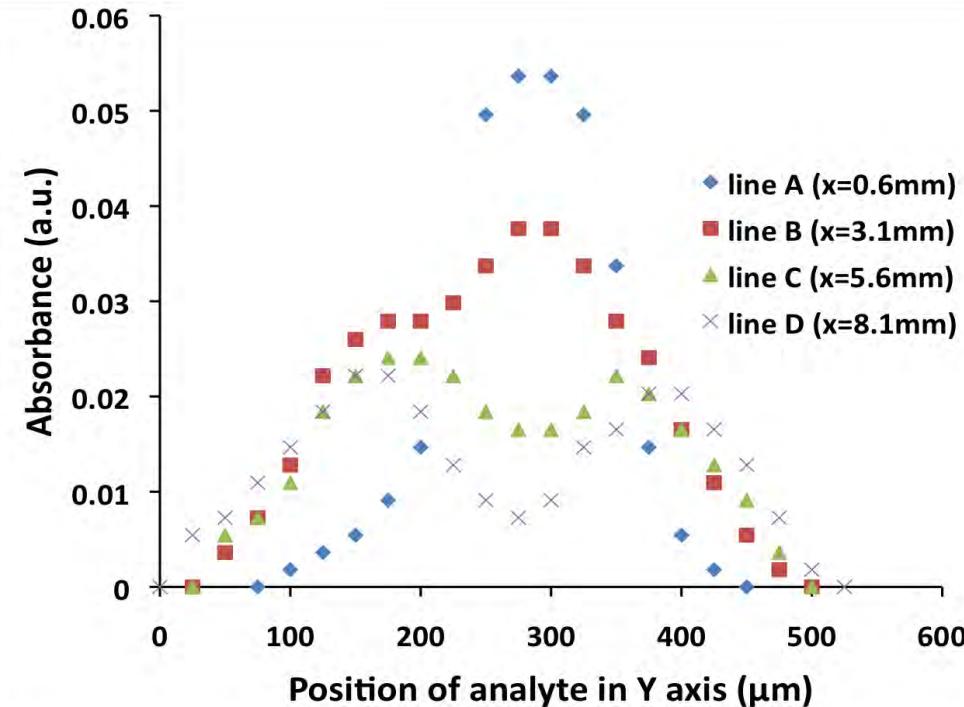


MIR Waveguides

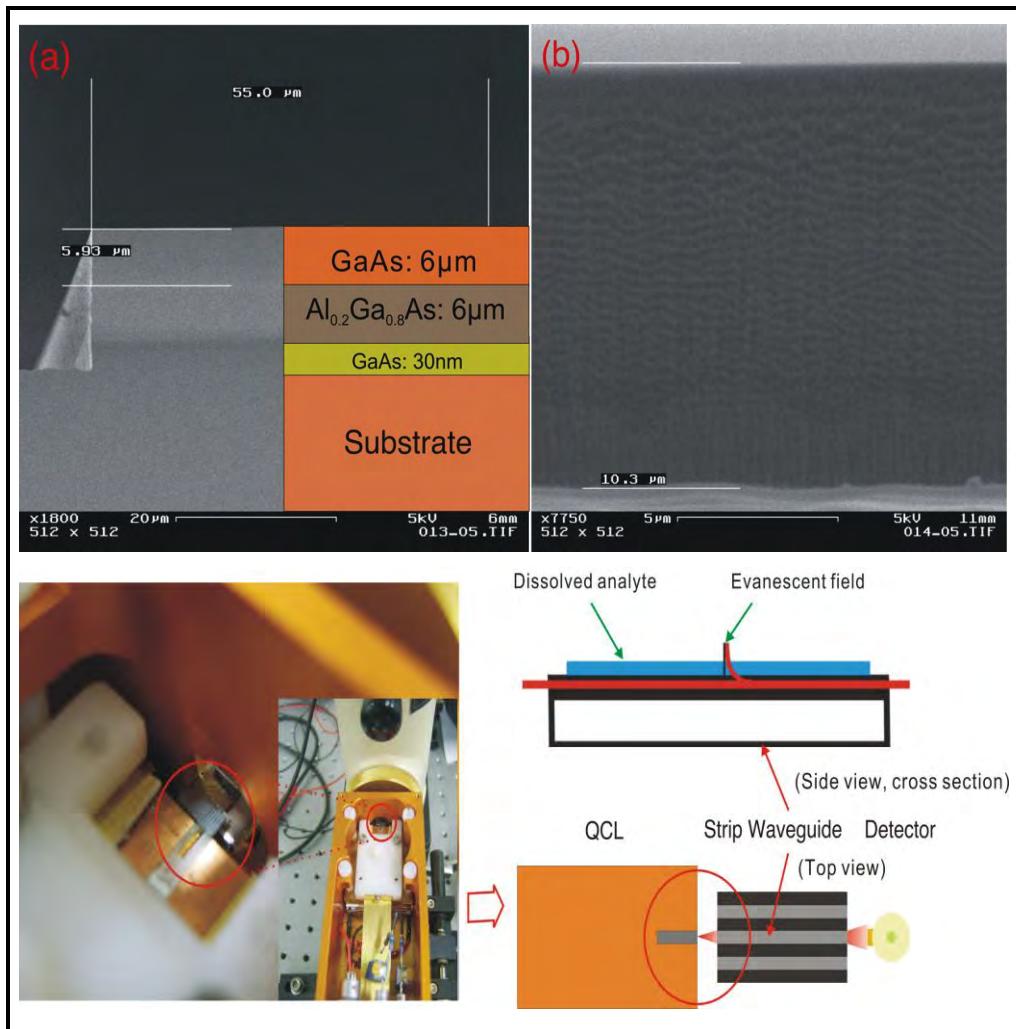
Towards superior mode control with GaAs/Al_{0.2}Ga_{0.8}As waveguides



- Frequency matched to QCL emission
- Well-defined evanescent field
- Superior mode control
- Toward the theoretical sensitivity limits of evanescent field sensing



QCL Combined with Strip Waveguides

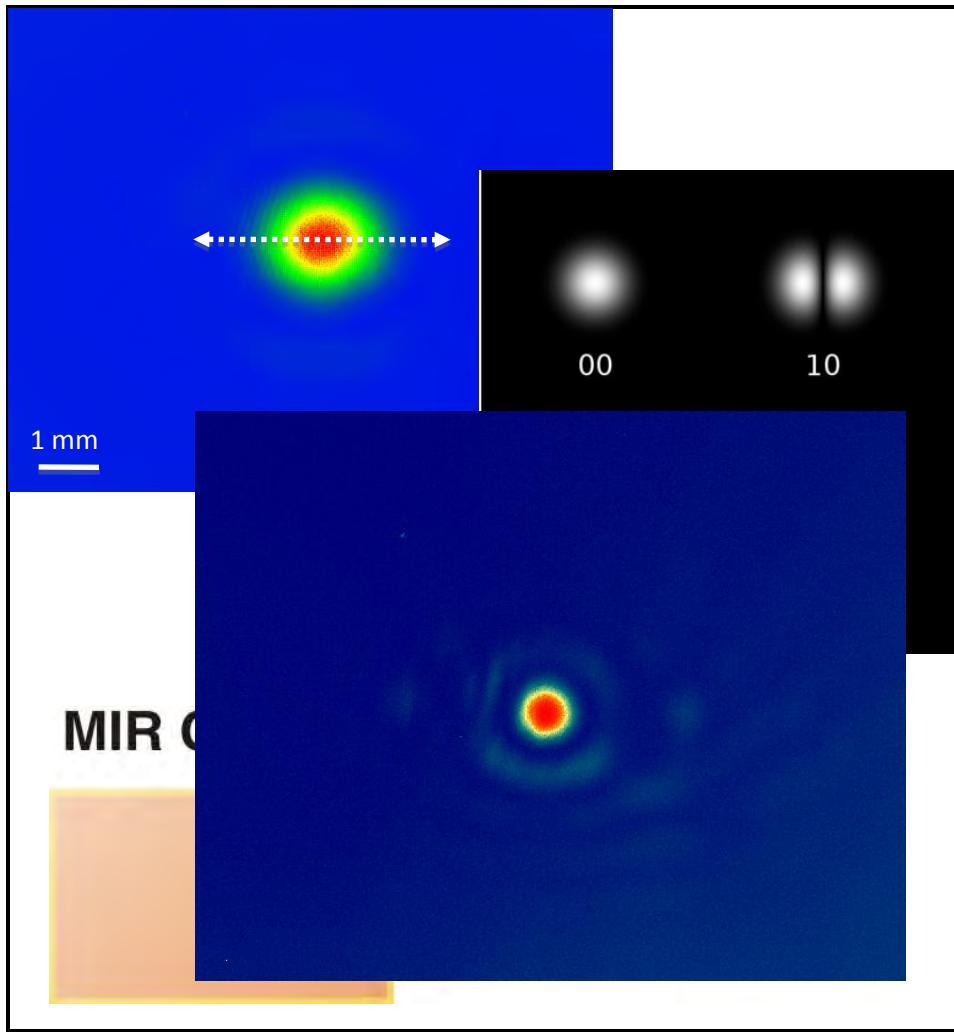


Chip-integrated IR devices

- Strip waveguide microfabrication via RIE (reactive ion etching)
- 200/100/50... μm wide waveguide strips
- QCL emission at 974 cm⁻¹ overlaps with absorption of analyte (acetic anhydride)

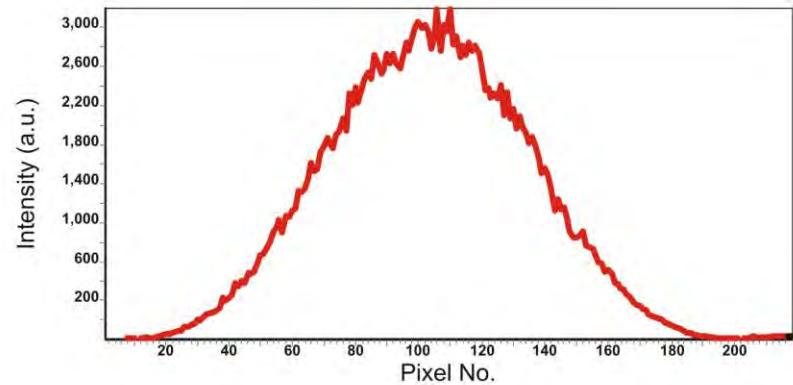
Sing Mode laser of EC-QCL

Mode analysis of EC-QCL with MIR camera



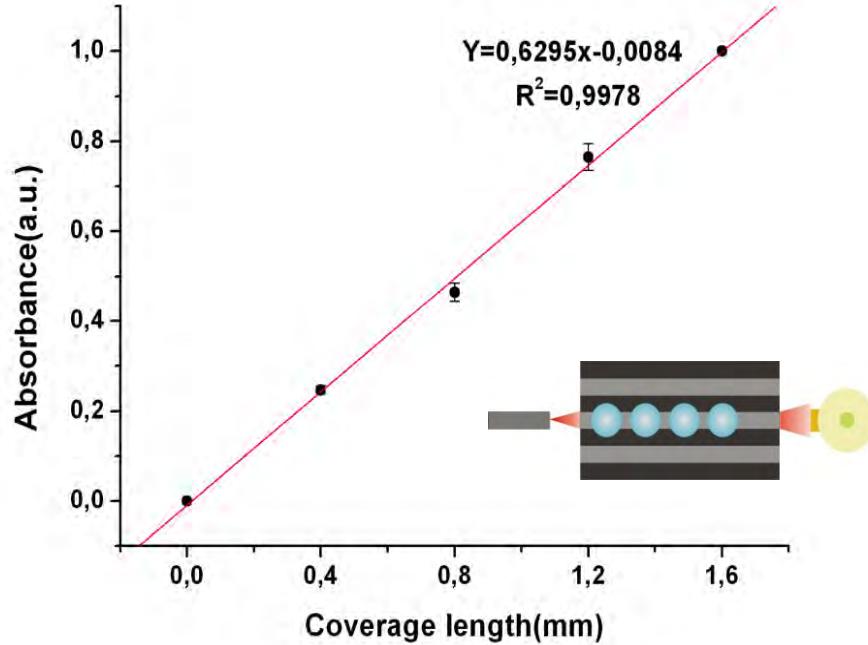
Beam Profile of EC-QCL in pulse mode

- Wavenumber: 1665 cm^{-1}
- Duty cycle: 1 %
- Repetition rate: 100 kHz
- Evidence of **single mode** pulse lasing of the EC-QCL ($1575\text{-}1735 \text{ cm}^{-1}$)



QCL Combined with Strip Waveguides

Calibration of coverage length



System response for GaAs strip waveguide as a function of the coverage length with linear fit. Each 2 nL droplet covered a diameter of 0.4 mm.

Measurements with strip waveguides

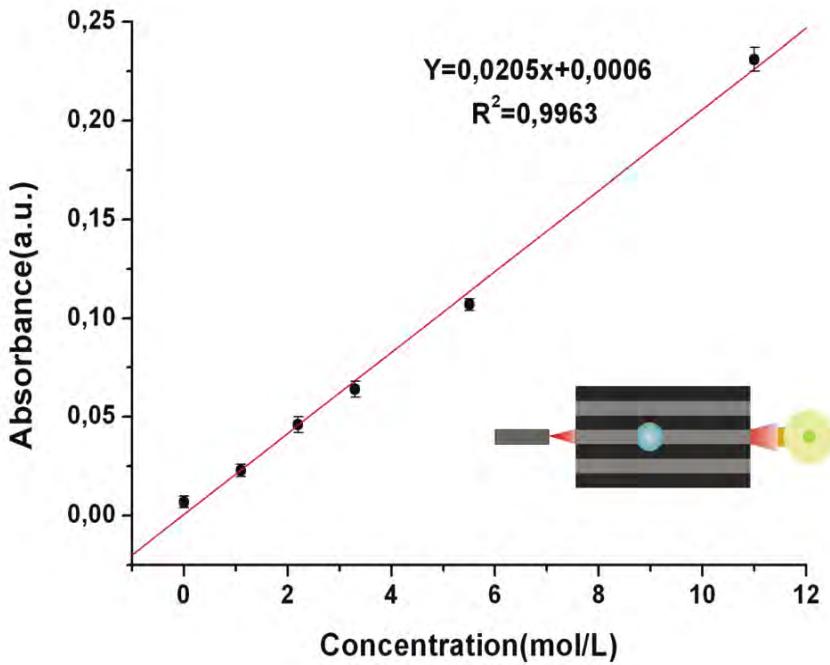
- Analyte: acetic anhydride
- 200 µm wide waveguide
- Micro-capillary used to generate 2 nL droplets
- pseudo Lambert-Beer law:

$$A = (\varepsilon \times c \times I) r$$

EW ratio: $r = I_e/I_0$
(I_e : evanescent field intensity, I_0 : total intensity of guided light)

QCL Combined with Strip Waveguides

Calibration of concentration



System response to diluted acetic anhydride in diethylene glycol monoethyl ether. Each 2 nL droplet covered a diameter of 0.4 mm.

Measurements with strip waveguides

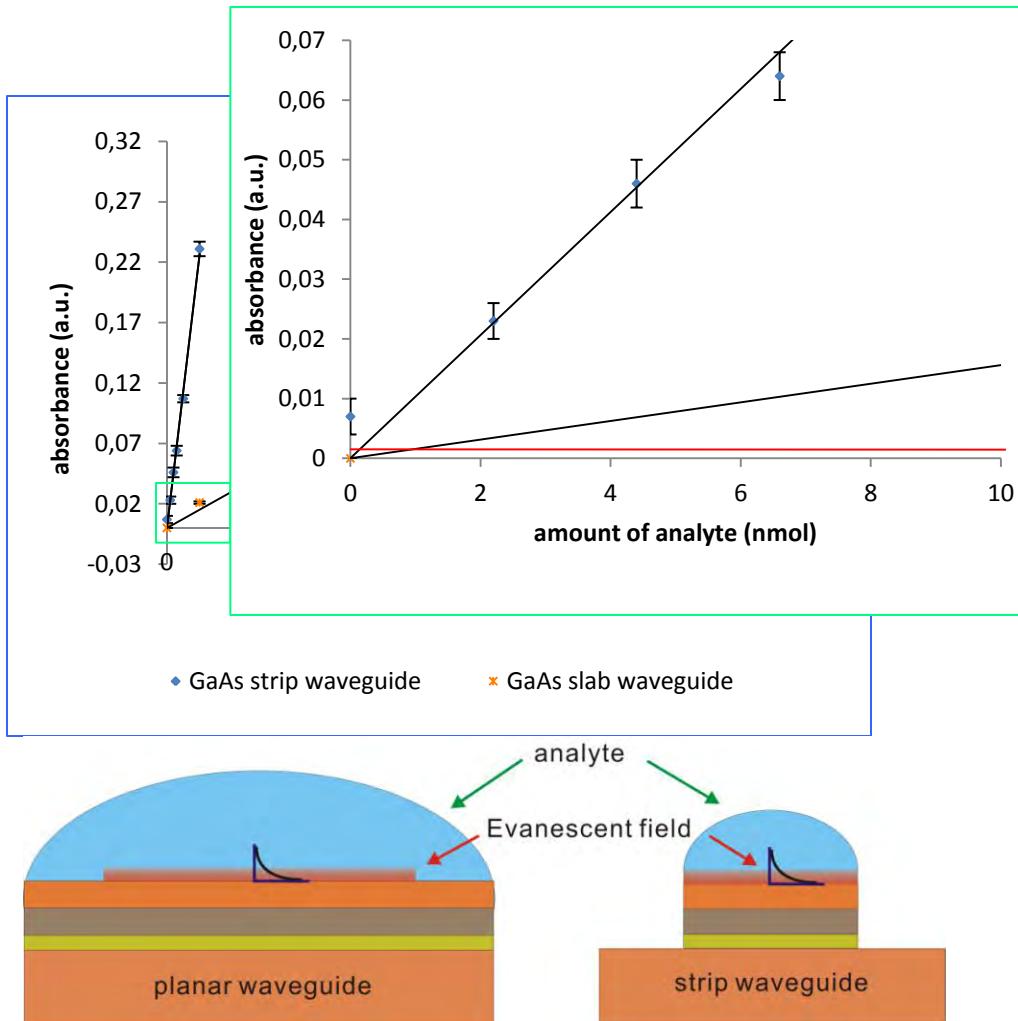
- Analyte: acetic anhydride
- 200 μm wide waveguide
- Micro-capillary used to generate 2 nL droplets
- pseudo Lambert-Beer law:

$$A = (\varepsilon \times c \times l) r$$

EW ratio: $r = I_e/I_0$
(I_e : evanescent field intensity, I_0 : total intensity of guided light)

QCL Combined with Strip Waveguides

Comparison strip waveguide vs. slab waveguide



Strip waveguide vs. slab waveguide

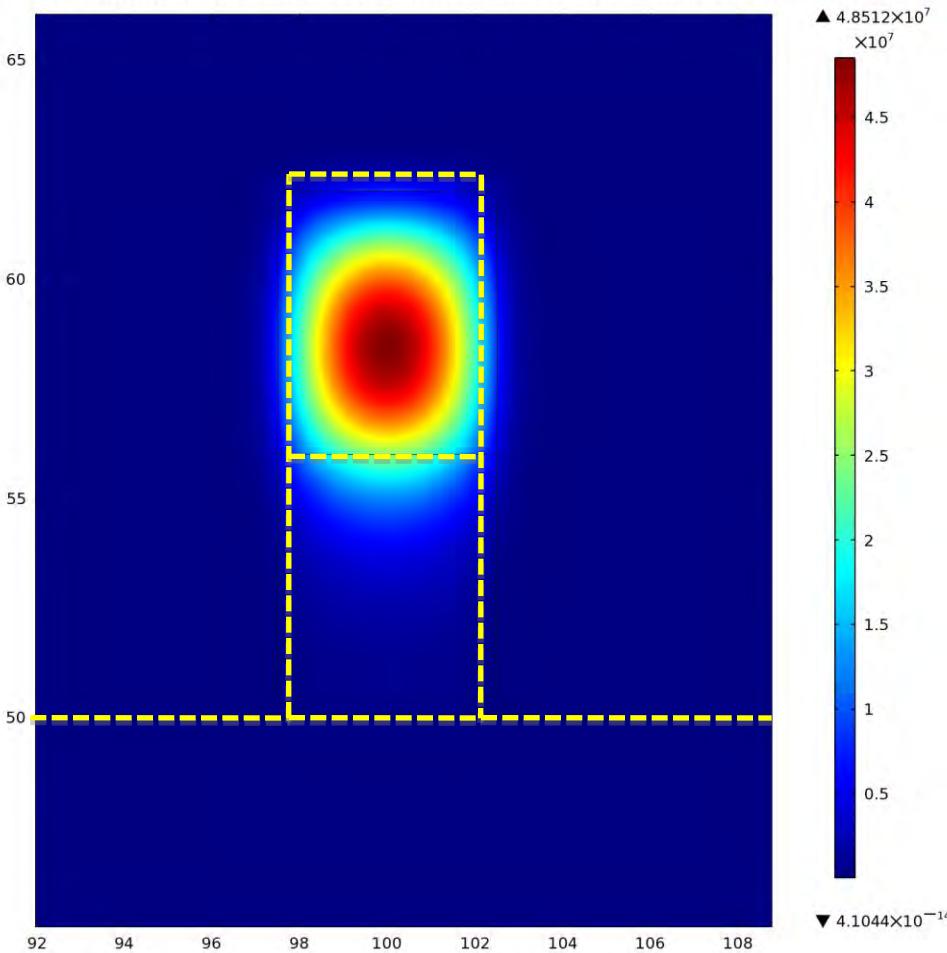
- CH₃-C bending vibration of acetic anhydride overlap with QCL emission
- 200 µm wide waveguide
- **LOD of 0.2 pL (2 pmol)**
- One order of magnitude improvement vs. slab waveguide
- Further improved sensitivity anticipated via narrowing strip width

Mode Analysis of GaAs/Al_{0.2}Ga_{0.8}As with COMSOL

Single Mode Waveguides



Effective mode index=3.22948 Surface: Electric field norm (V/m)



RF module, Electromagnetic Waves (emw).

Geometry and Material parameters:

Core: 6 um GaAs, n=3.3

Clad: 6 um Al_{0.2}Ga_{0.8}As, n=3.2

Wafer: GaAs (doped), n= 3.2

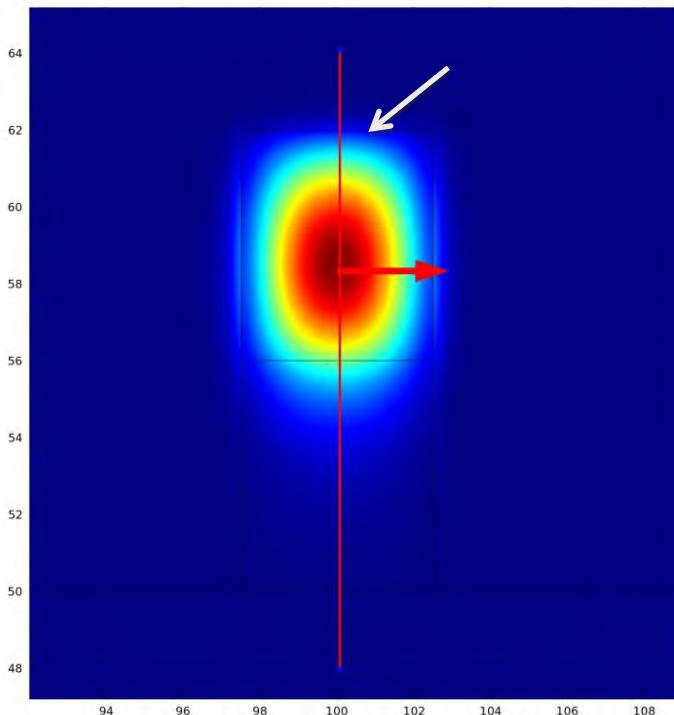
Air: n=1

Width of WG: 5 um

Wavelength: 6.01 um (1665 cm⁻¹)

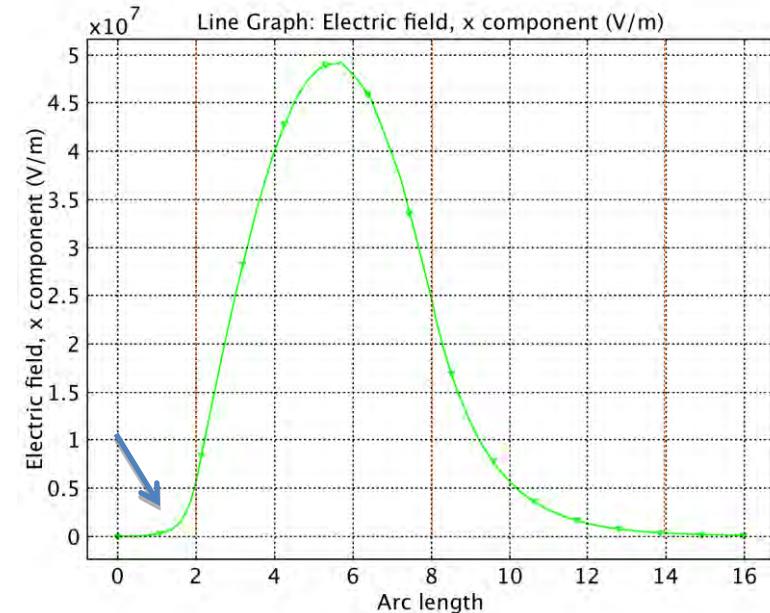
Single Mode: TEM (0,0)

Mode Analysis of GaAs/Al_{0.2}Ga_{0.8}As



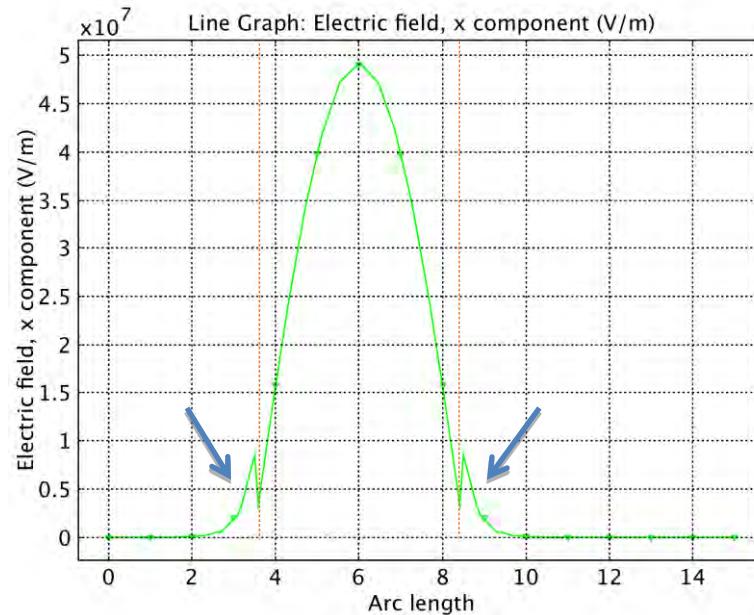
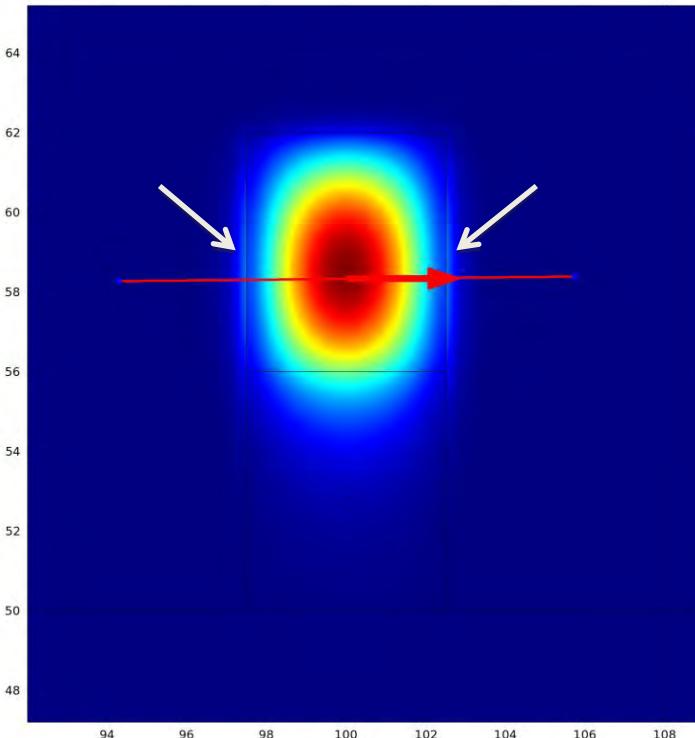
2D mode analysis with strip width of 5 μm
Red line stands for the cross-section in y-axis
Red arrow stands for the direction of electrical field: E_x along x-axis.

Intensity Fraction of evanescent field over the total beam is calculated to be 0.06 % along the cross-section.



E_x distribution along the cross-section with effective mode index of $n_{\text{eff}} = 3.22$.
Arc length (0 - 2): evanescent field, (2 - 8): core, (8 - 14): cladding, (14 - 16): substrate.

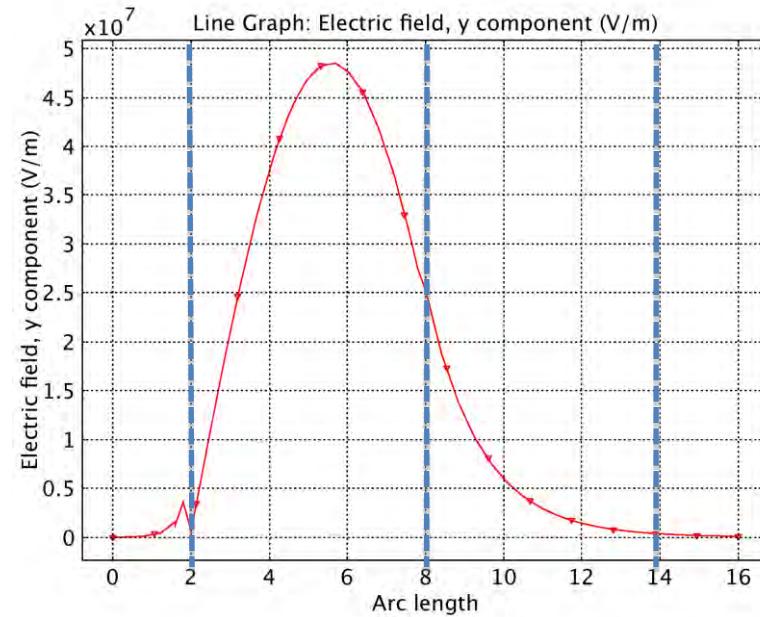
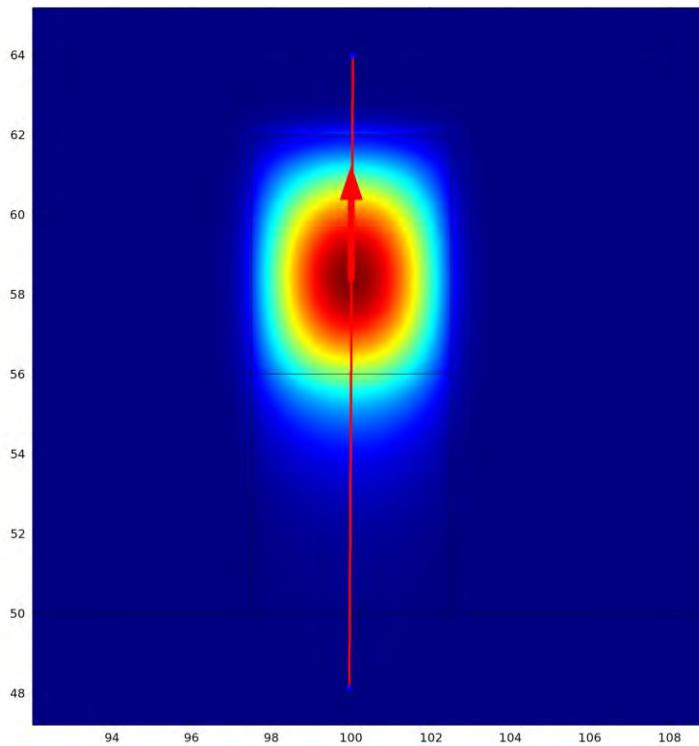
Mode Analysis of GaAs/Al_{0.2}Ga_{0.8}As



E_x distribution with $n_{\text{eff}} = 3.22$. There is discontinuity of E_x on interface between the core and air ($x = 3.5, 8.5$).

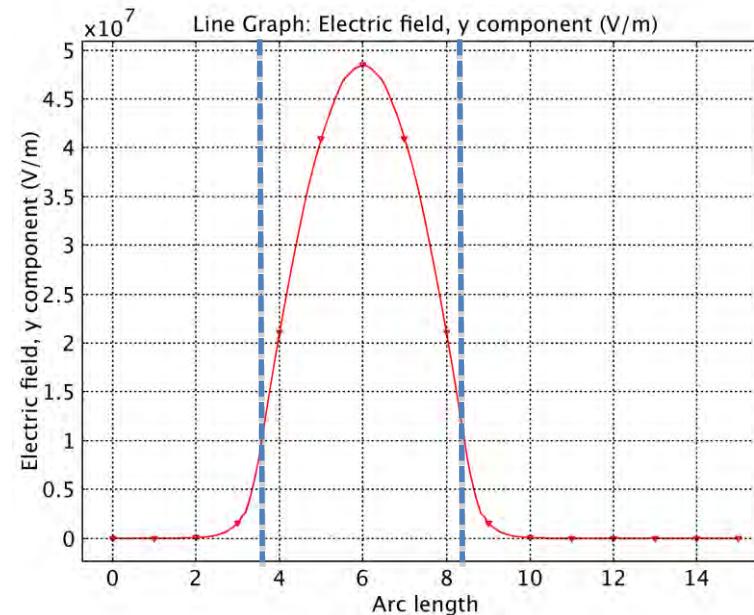
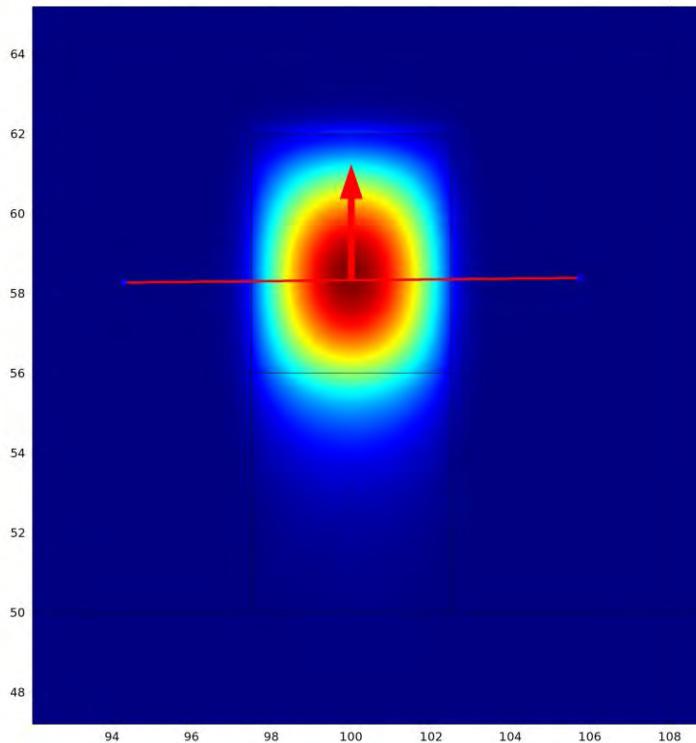
The penetration depth D_p of evanescent field is estimated to be 1 μm in the simulation. The fraction of evanescent field is calculated to be 0.3 % for each interface along the cross-section.

Mode Analysis of GaAs/Al_{0.2}Ga_{0.8}As with COMSOL



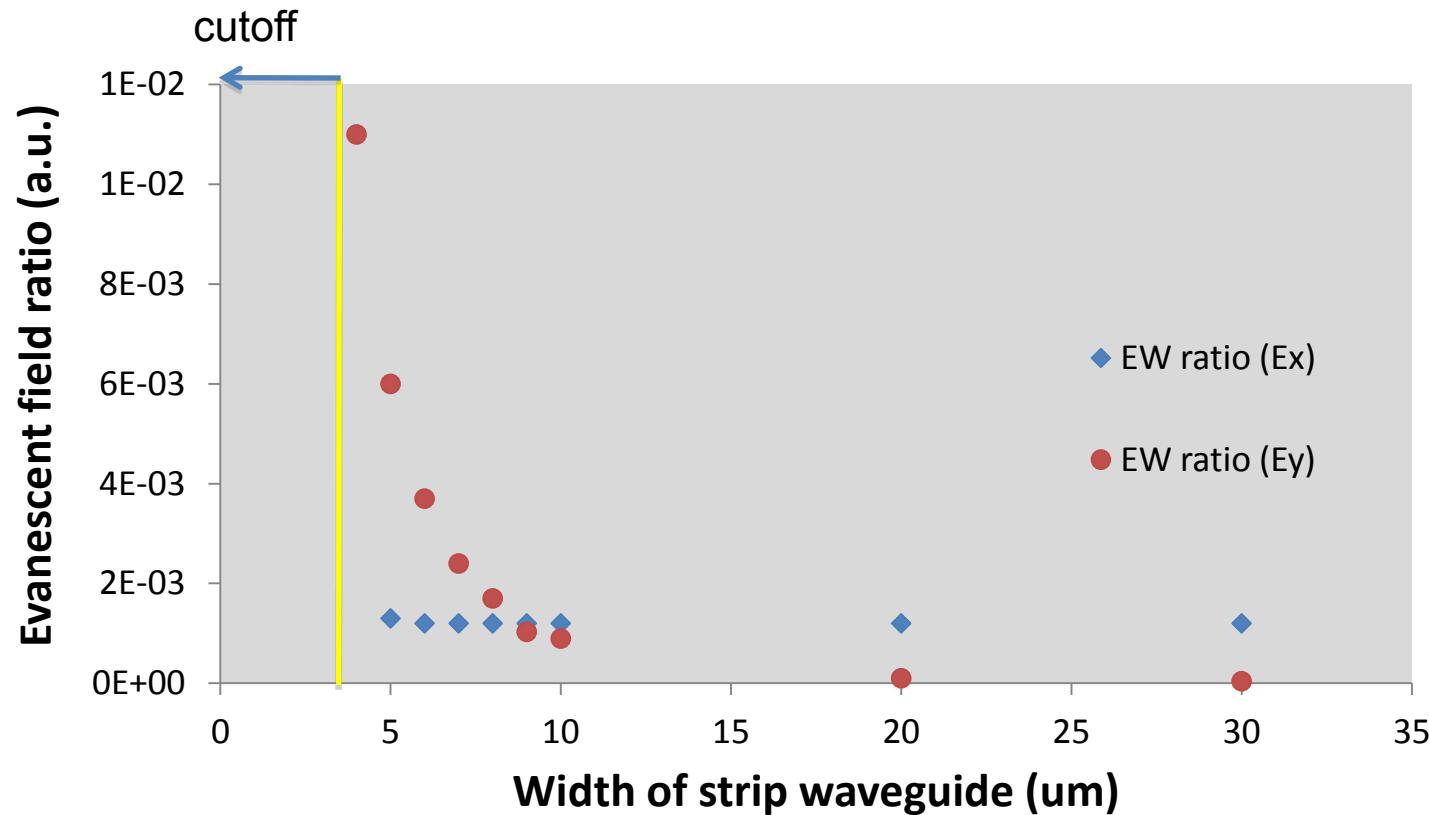
E_y distribution along the line is analyzed in the diagram on the right ($n_{eff1}=3.22948$). There is discontinuity of E_y on interface of vacuum and the core ($x=2$ um).

Mode Analysis of GaAs/Al_{0.2}Ga_{0.8}As with COMSOL



E_y distribution along the line is analyzed in the diagram on the right ($n_{\text{eff}1}=3.22948$). There is no discontinuity of E_y on interface of vacuum and the core ($x=3.5$ and 8.5). The penetration depth D_p of evanescent field is around 1 um.

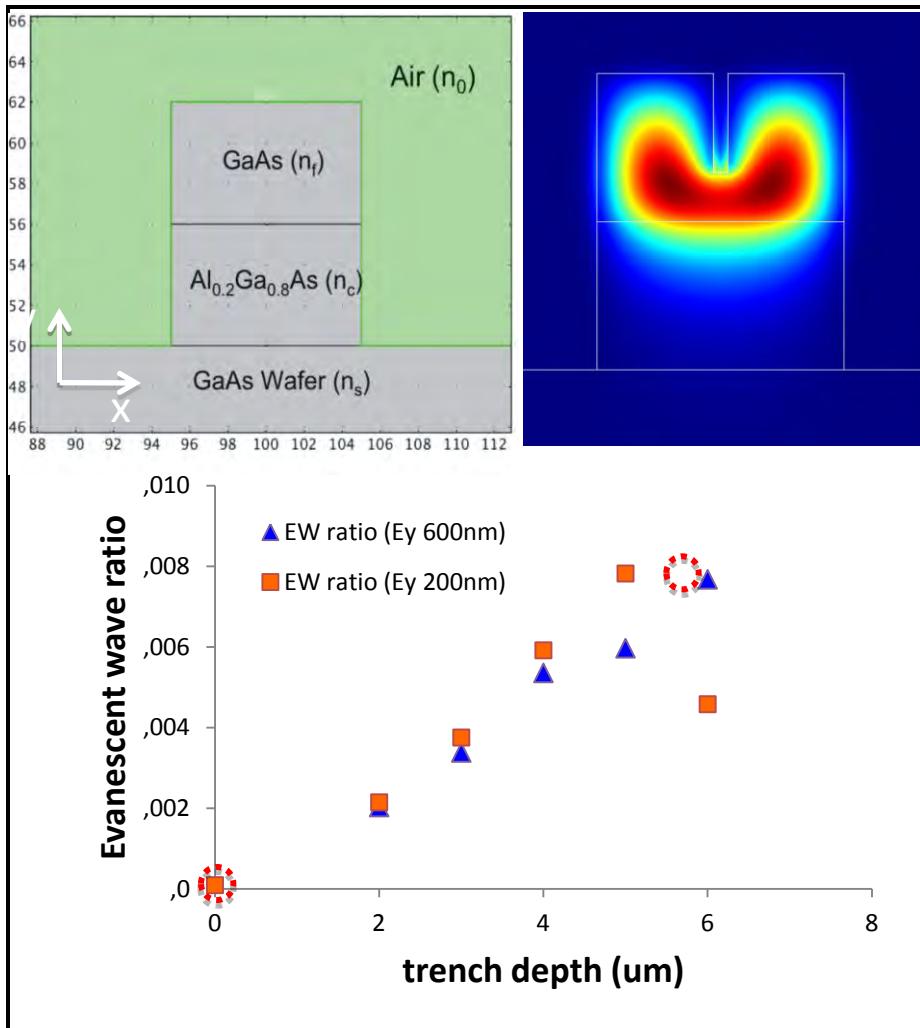
Mode Analysis of GaAs/Al_{0.2}Ga_{0.8}As



The $E_y(0, 0)$ behaves as an exponential curve and the EW ratio achieves $r_e > 1\%$ with cutoff width $D_c = 4 \text{ um}$ at 1665 cm^{-1} .

MIR Slot Waveguides

Advanced waveguide design with FEM simulations



SlotStrip waveguide vs. strip waveguide

↓
WG width: 10 μm

↓
Trench width: 200 / 600 nm

→ pseudo Lambert-Beer law:
$$A = (\epsilon cl) r$$

→ EW ratio: $r = I_e/I_0$
(I_e : evanescent field intensity, I_0 : total intensity of guided light)

→ Enhancement factor: up to 1-2 orders of magnitude expected!



- Simulation studies on GaAs/AlGaAs strip waveguide
- Optimization of single mode MIR strip waveguide
Simulation & experiment
- 3-D Simulation of beam propagation in strip waveguide
- Resonator based waveguide design

Acknowledgements



Prof. Dr. B. Mizaikoff



Dr. P. Michler

Dr. R. Rossbach

Dr. M. Jetter

FIB Center UUlm

Dr. C. Kranz





Thanks for your attention!

Simulation Study

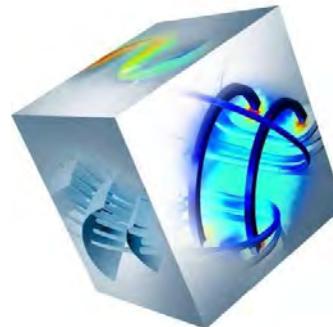
COMSOL – RF-Module



The Electromagnetic Waves interface, analyzes frequency domain electromagnetic waves, and uses time-harmonic and eigenfrequency/eigenmode studies.

It Provides:

- Flexible what-if-scenarios
- 1. Physics Solution
- 2. Solving Equations
- 3. 3.



Work process:

1. Model Meshing
2. Applicate of material properties
3. Add the Physics
4. Defining the boundary conditions
5. Compute

Maxwell Equations

Divergence equations Curl equations

Electric: $\nabla \cdot \mathbf{D} = \rho$

$$\nabla \times \mathbf{E} = -\frac{\partial \mathbf{B}}{\partial t}$$

Magnetic: $\nabla \cdot \mathbf{B} = 0$

$$\nabla \times \mathbf{H} = \frac{\partial \mathbf{D}}{\partial t} + \mathbf{J}$$

\mathbf{D} = Electric flux density

\mathbf{B} = Magnetic flux density

\mathbf{E} = Electric field vector

\mathbf{H} = Magnetic field vector

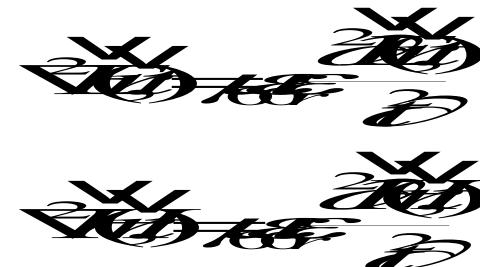
ρ = charge density

\mathbf{J} = current density

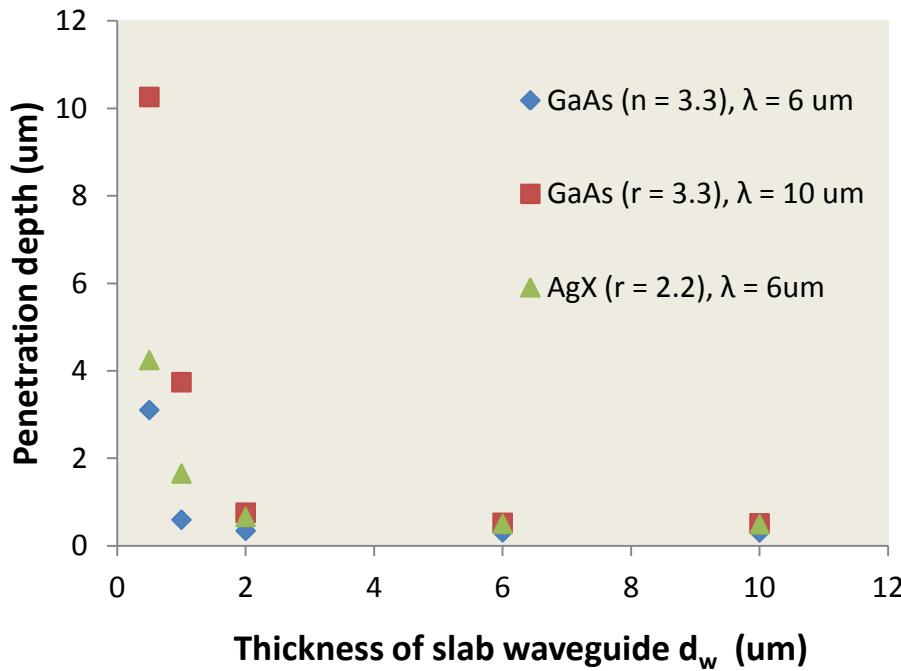
Wave Equations

Electric:

Magnetic:



Mode Analysis of GaAs/Al_{0.2}Ga_{0.8}As with COMSOL



Waveguide structure: Slab waveguide (WG)

Polarization: TM

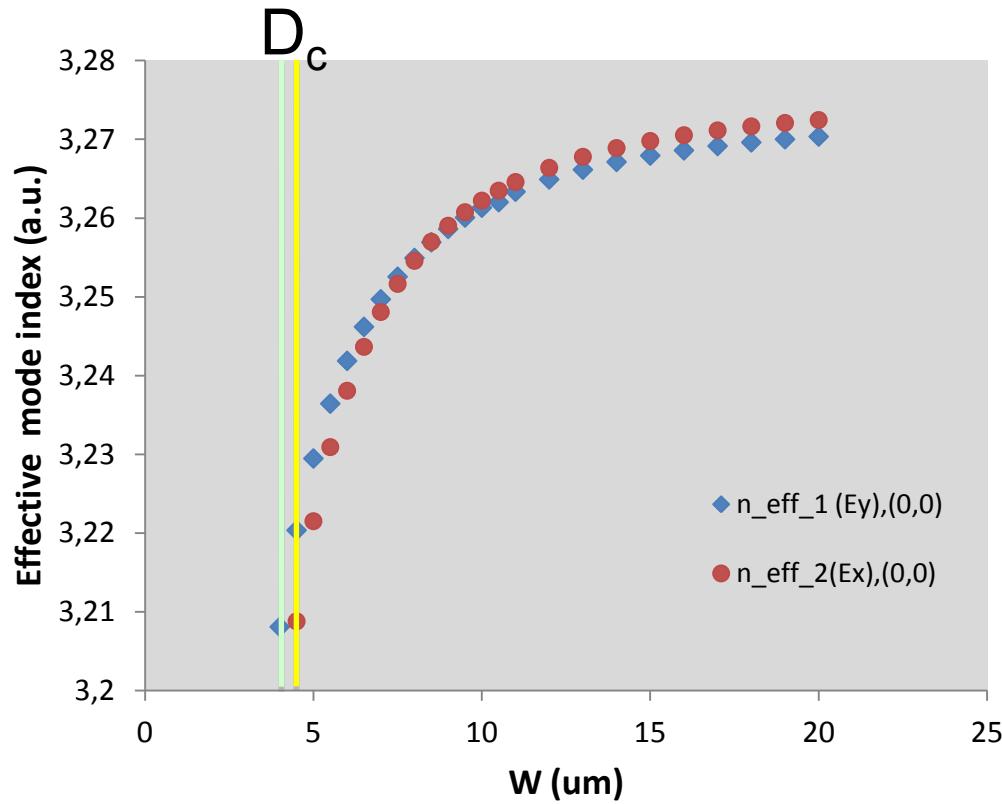
Mode index: $m = 0$

Refractive Index of GaAs: $n_1 = 3.3$

Refractive Index of air: $n_2 = 1$

Slab waveguide with symmetric structure does not own cut-off thickness. Penetration depth D_p show dramatical increase as thickness of waveguide narrows down to sub-wavelength range.

Mode Analysis of GaAs/Al_{0.2}Ga_{0.8}As with COMSOL

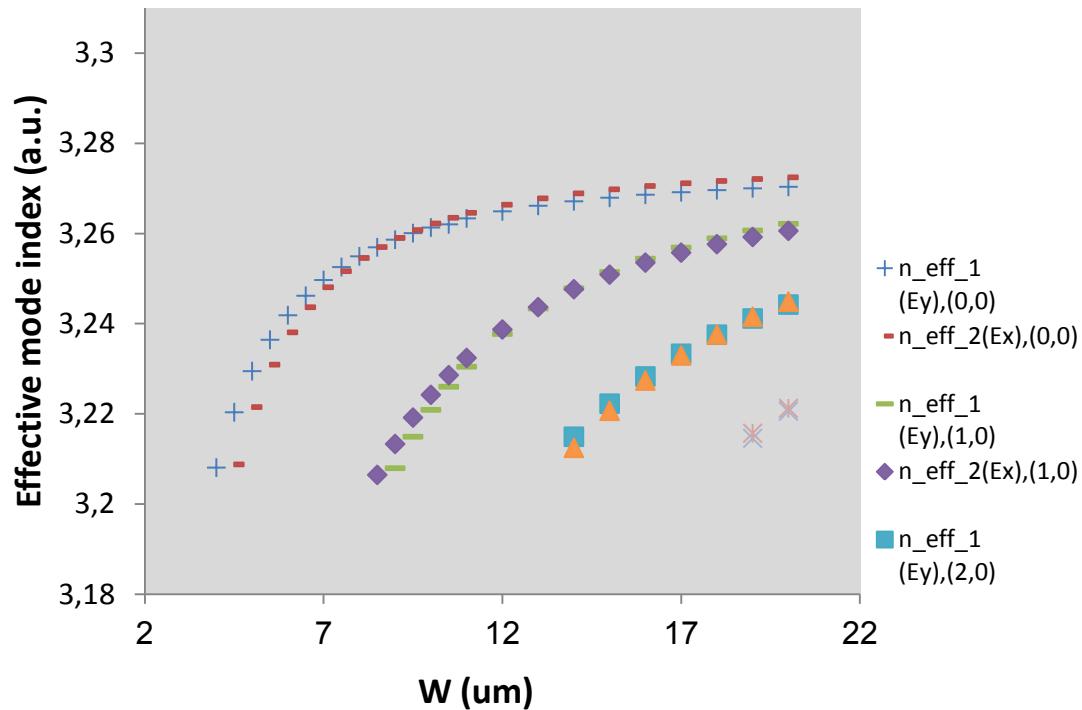


Cutoff width D_c of strip WG at 1665 cm⁻¹ are 4.5 um for E_y and 5 um for E_x TE (0,0) mode respectively.

Effective mode index n_{eff} must fulfill the range: $n_f > n_{\text{eff}} > n_c$

As strip narrows down to D_c , n_{eff} approach to n_c .

Mode Analysis of GaAs/Al_{0.2}Ga_{0.8}As with COMSOL



The strip waveguide will support higher order modes of light as w increases.

According to the simulation results from the diagram on the left, in order to avoid the generation of higher order modes of light, the width should be confined within 8 um (D_c in $E_x(1.0)$ mode).